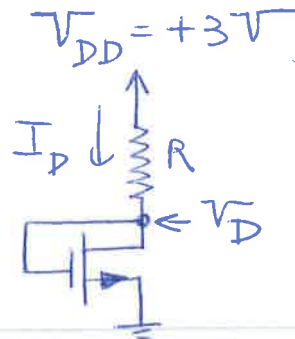


Name:

(200)  
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ELECTRONICS I  
December 5th, 2007

1. (25 pts) Design the circuit below to obtain a current  $I_D$  of  $80 \mu\text{A}$ . Find the value of the resistor  $R$  and the value of the drain voltage. For this NMOS transistor, use  $V_t = 0.6\text{V}$ ,  $\mu_n C_{ox} = 200 \mu\text{A}/\text{V}^2$ ,  $L = 0.8 \mu\text{m}$  and  $W = 4 \mu\text{m}$ . Neglect the short-channel effect, i.e., assume  $\lambda = 0$ .



$V_{DS} = 0 \rightarrow V_D = V_G \rightarrow$  FET is operating in the saturation regime.

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_t)^2 \quad (+5)$$

$$\rightarrow V_{GS} - V_t = \sqrt{\frac{2I_D}{\mu_n C_{ox} (W/L)}} = 0.4\text{V} \quad (+5)$$

$$V_{GS} = V_t + (V_{GS} - V_t) = 0.6 + 0.4 = 1\text{V} \quad (+5)$$

$$\rightarrow V_D = V_G = +1 \quad (+5)$$

$$\rightarrow R = \frac{(V_{DD} - V_D)}{I_D} = \frac{3 - 1}{0.080} = 25\text{k}\Omega \quad (+5)$$

2. (25 pts) A particular enhancement MOSFET has a  $V_t$  of 1 V and  $k_n' \left(\frac{W}{L}\right) = 0.1 \text{ mA/V}^2$  and  $\lambda = 0$ . It is to be operated in the saturation regime.

- To be operated with  $I_D = 0.2 \text{ mA}$ , find the required  $V_{GS}$  and the minimum required  $V_{DS}$ .
- Repeat the previous question with  $I_D = 0.8 \text{ mA}$ .

a

$$I_D = \frac{k_n'}{2} \frac{W}{L} (V_{GS} - V_t)^2 \quad (+3)$$

$$0.2 \cdot 10^{-3} = \frac{1}{2} \cdot 0.1 \cdot 10^{-3} (V_{GS} - 1)^2$$

$$\rightarrow V_{GS} - 1 = 2 \Rightarrow V_{GS} = 3V \quad (+4)$$

$$V_{DS \text{ min}} = V_{GS} - V_t = 3 - 1 = 2V \quad (+3)$$

12.5

+2.5

b

$$I_D = 0.8 \text{ mA}$$

$$\rightarrow 0.8 = \frac{1}{2} \cdot 0.1 (V_{GS} - 1)^2 \quad (+3)$$

$$V_{GS} - 1 = 4 \Rightarrow V_{GS} = 5V \quad (+4)$$

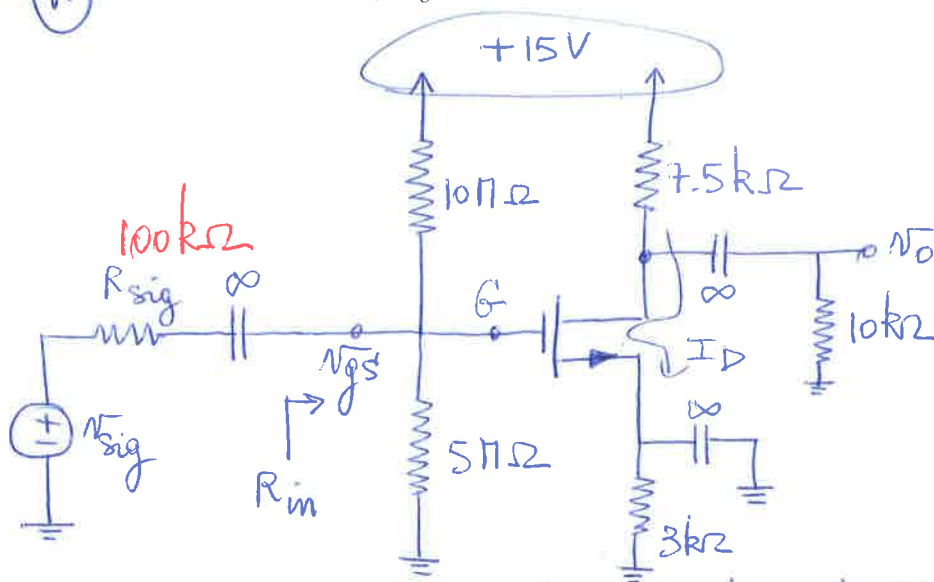
$$V_{DS \text{ min}} = V_{GS} - V_t = 5 - 1 = 4V \quad (+3)$$

12.5

+2.5

4. (30 pts) In the circuit amplifier below, the signal source is coupled to the gate through a very large capacitor (i.e., which behaves as a short at the frequency of operation of the signal source). The output voltage is coupled to the load via a coupling capacitor which also behaves as a short at the frequency of operation of the amplifier.

- (a) • Is the amplifier circuit, (a) a common source, (b) a common gate, or (c) a common drain configuration?
- (b) • If the transistor has a  $V_t = 1\text{ V}$  and  $k_n' (\frac{W}{L}) = 2.0\text{ mA/V}^2$ , check that the biasing configuration with the four resistors establish a drain current of  $1\text{ mA}$ , a  $V_{GS}$  value of  $2\text{ V}$ , and a drain voltage value of  $7.5\text{ V}$ . Assume  $\lambda = 0$ .
- (c) • Using the previous results, calculate the transconductance  $g_m$  in  $\text{mS}$  and the value of  $r_o$ . The latter will be included in the small AC circuit model to be analyze next. Use  $V_A = 100\text{ V}$ .
- (d) • Draw the complete small signal equivalent circuit for the amplifier. (use hybrid- $\pi$  model)
- (e) • Calculate the input resistance of that amplifier. include effects of  $r_o$ .
- (f) • Calculate  $v_{gs}/v_{sig}$ .
- (g) • Calculate  $v_o/v_{gs}$ .
- (h) • Finally, calculate  $v_o/v_{sig}$ .



(b)  $V_G = \left(\frac{5}{15}\right) 15 = 5\text{ V}$  (+1)

[Non saturation]

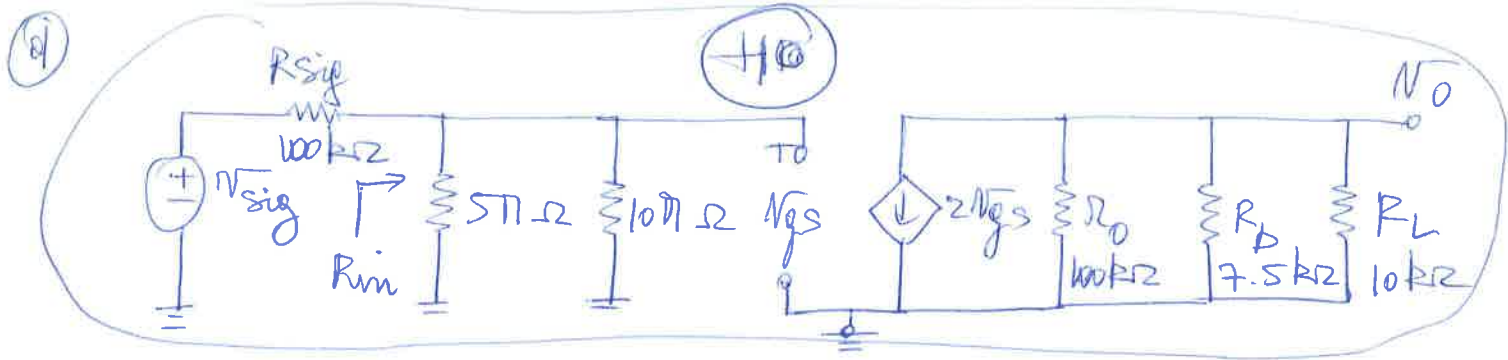
$$I_D = \left(\frac{k_n'}{2}\right) \frac{W}{L} (V_{GS} - V_t)^2$$

$$I_D = \frac{2}{2} (2 - 1)^2 = 1\text{ mA} \quad (+2)$$

$$V_D = 15 - 7.5\text{ k}\Omega (1\text{ mA}) = 7.5\text{ V} \quad (+2)$$

(c)  $g_m = k_n' \frac{W}{L} (V_{GS} - V_t)$  (+1)  
 $= 2\text{ mA/V}^2 (2 - 1) = 2\text{ mS}$

$$r_o = \frac{V_A}{I_D} = \frac{100}{1\text{ mA}} = 100\text{ k}\Omega \quad (+1)$$



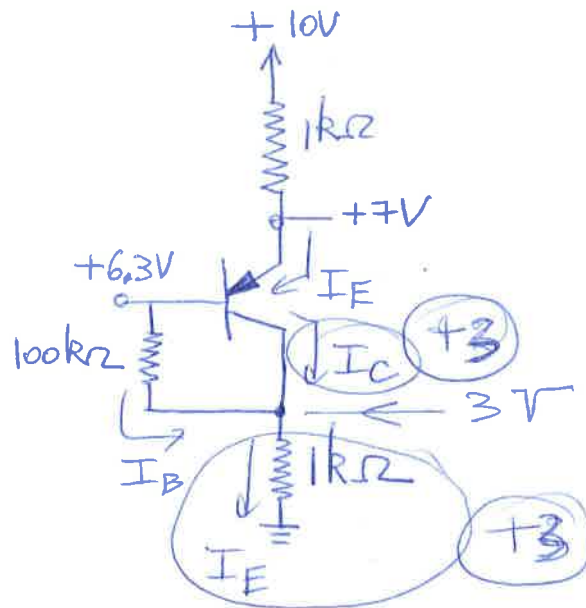
(e)  $R_{in} = (50\text{k}\Omega // 10\text{k}\Omega) = 3.33\text{k}\Omega$  (+3)

(f)  $\frac{v_{gs}}{v_{sig}} = \frac{R_{in}}{R_{sig} + R_{in}} = \frac{3.33}{0.1 + 3.33} = 0.97\text{ V/V}$  (+3)

(g)  $\frac{v_o}{v_{gs}} = -2 (r_o // R_D // R_L) = -2 \sqrt[ms]{(4.1\text{k}\Omega)} = -8.2\text{ V/V}$  (+3)

$\frac{v_o}{v_{sig}} = -7.95\text{ V/V}$  (+2)

5. (20 pts) Measurements on the circuit below produce the values of the labeled voltages as indicated. Find the corresponding value of  $\beta$  for that transistor.



$$I_E = \frac{10 - 7}{1k\Omega} = 3 \text{ mA} \quad (+4)$$

$$I_B = \frac{6.3 - 3}{100k\Omega} = \frac{3.3}{100} \text{ mA} = 33 \mu\text{A} \quad (+4)$$

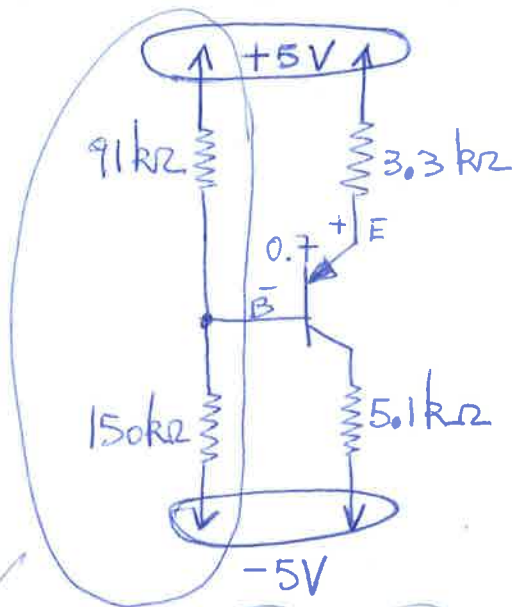
$$I_C + I_B = I_E \quad (+2)$$

$$I_E = \frac{(\beta + 1) I_B}{\#} \Rightarrow \beta + 1 = \frac{I_E}{I_B}$$

$$\beta = \frac{I_E}{I_B} - 1 = \frac{3 \cdot 10^{-3}}{33 \cdot 10^{-6}} - 1 \quad (+2)$$

$$\beta = \frac{10^3}{11} - 1 \approx 90 \quad (+2)$$

6. (20 pts) For the circuit shown below, find the value of the emitter current using the "loop equation". Hint: first replace the two leftmost resistors by their Thevenin equivalent. Remember "no rabbit out of the hat!". You must show how you derive the loop equation. Assume  $V_{EB} = 0.7V$  and  $\beta = 100$ .



$$I_B = \frac{I_E}{\beta + 1}$$

$$\beta = 100$$

$$V_{Th} = \left( \frac{150}{91 + 150} \right) 10V - 5V = 1.22V$$

$$R_{Th} = (91 \parallel 150) k\Omega = 56.63 k\Omega$$

$$5 - 3.3 I_E - 0.7 - R_{Th} \frac{I_E}{\beta + 1} = V_{Th}$$

$$\rightarrow I_E = \frac{5 - 0.7 - V_{Th}}{3.3 + \frac{R_{Th}}{\beta + 1}} = \frac{3.08}{3.86}$$

$$\rightarrow I_E = 0.798 \text{ mA}$$

